

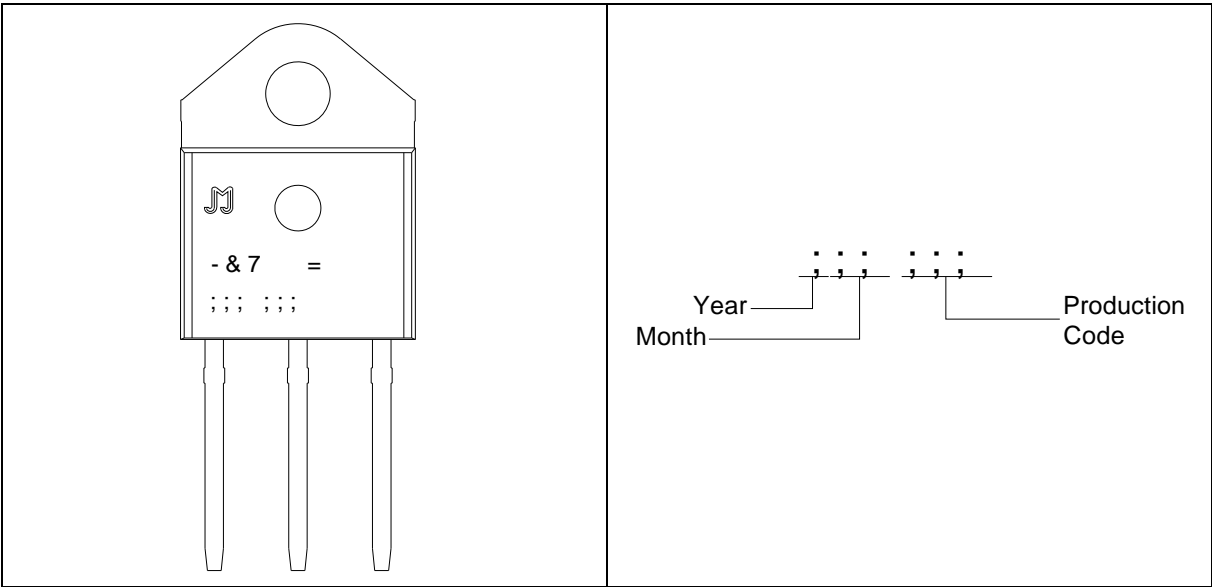
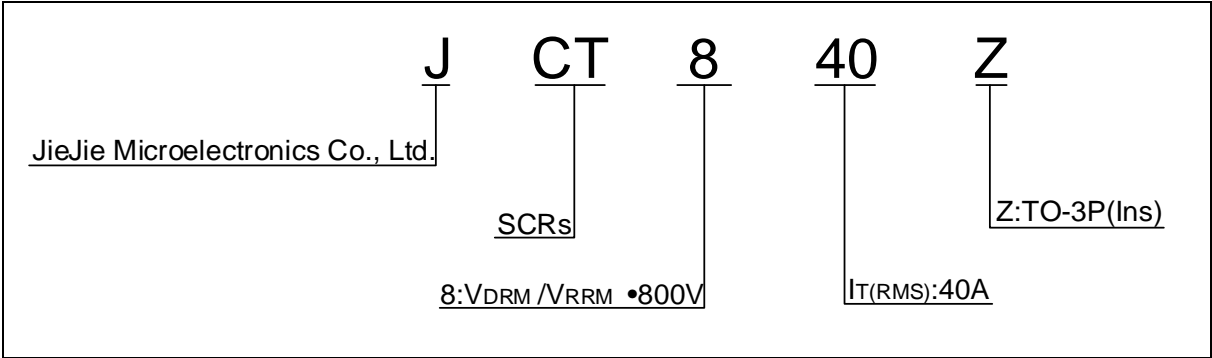


# JCT840Z

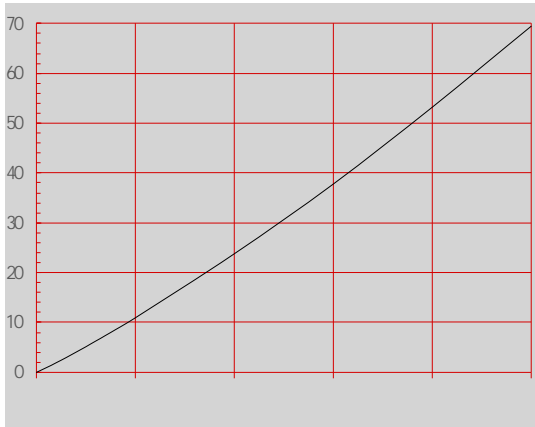


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Peak gate current ( $t_p=20\mu s$ , $T_j=125$ )	$I_{GM}$	10	A
Average gate power dissipation ( $T_j=125$ )	$P_{G(AV)}$	1	W
Peak gate power	$P_{GM}$	20	W
Peak pulse voltage ( $T_j$ )			

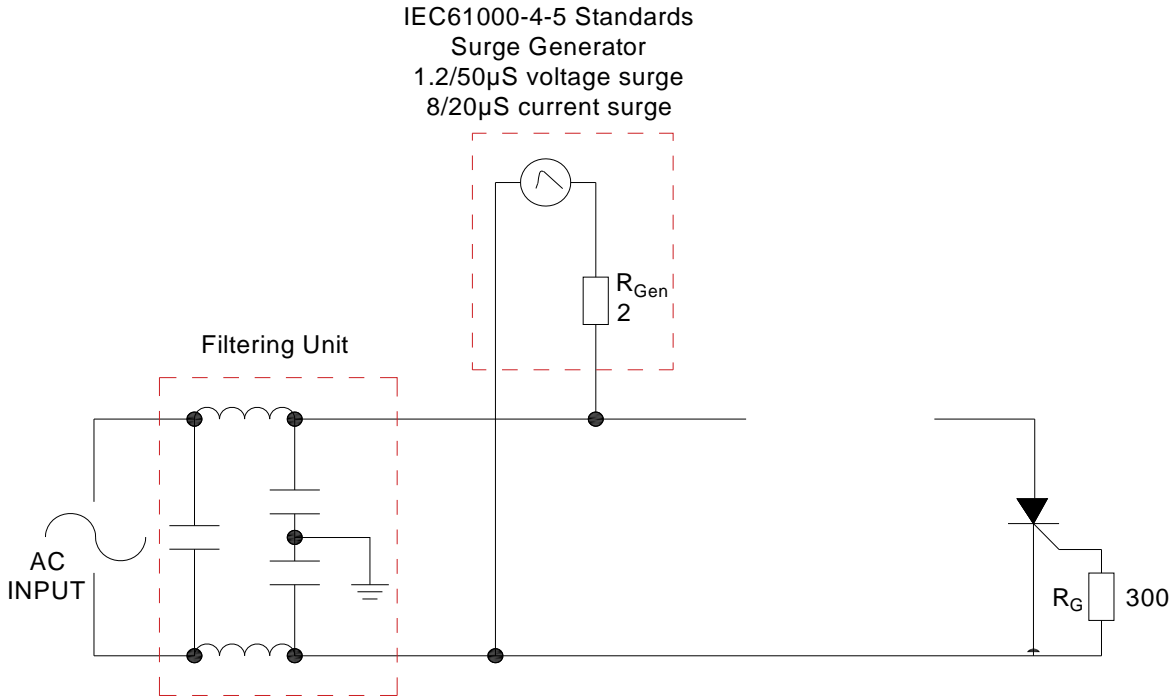


**FIG.1:** Maximum power dissipation versus RMS on-state current



**FIG.2:** RMS on-state current versus case temperature

FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.



Order code	Voltage $V_{DRM}/V_{RRM}$ (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
JCT840Z	800	35	TO-3P(Ins)	30	Tube

### Document Revision History

Date	Revision	Changes
Apr.13, 2023	A.1.0	Last update
Oct.16, 2025	A.1.1	Revise PACKAGE MECHANICAL DATA



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